

CM1293A

Table 1. PIN DESCRIPTIONS

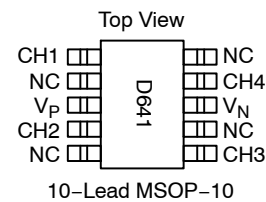
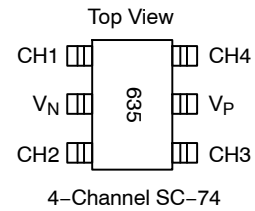
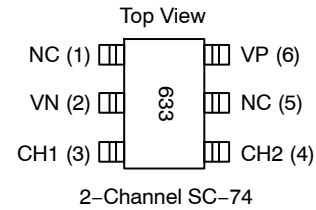
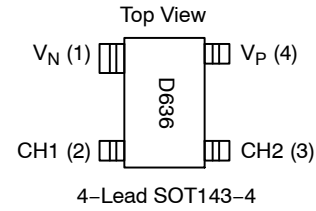
2-Channel, 4-Lead SOT143-4 Package (CM1293A-02SR)			
Pin	Name	Type	Description
1	V _N	GND	Negative Voltage Supply Rail
2	CH1	I/O	ESD Channel
3	CH2	I/O	ESD Channel
4	V _P	PWR	Positive Voltage Supply Rail

2-Channel, SC-74 Package (CM1293A-02SO)			
Pin	Name	Type	Description
1	NC	–	No Connect
2	V _N	GND	Negative Voltage Supply Rail
3	CH1	I/O	ESD Channel
4	CH2	I/O	ESD Channel
5	NC	–	No Connect
6	V _P	PWR	Positive Voltage Supply Rail

4-Channel, SC-74 Package (CM1293A-04SO)			
Pin	Name	Type	Description
1	CH1	I/O	ESD Channel
2	V _N	GND	Negative Voltage Supply Rail
3	CH2	I/O	ESD Channel
4	CH3	I/O	ESD Channel
5	V _P	PWR	Positive Voltage Supply Rail
6	CH4	I/O	ESD Channel

4-Channel, 10-Lead MSOP-10 Package (CM1293A-04MR)			
Pin	Name	Type	Description
1	CH1	I/O	ESD Channel
2	NC	–	No Connect
3	V _P	PWR	Positive Voltage Supply Rail
4	CH2	I/O	ESD Channel
5	NC	–	No Connect
6	CH3	I/O	ESD Channel
7	NC	–	No Connect
8	V _N	GND	Negative Voltage Supply Rail
9	CH4	I/O	ESD Channel
10	NC	–	No Connect

PACKAGE / PINOUT DIAGRAM



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SPECIFICATIONS

Table 2. ABSOLUTE MAXIMUM RATINGS

Parameter	Rating	Units
Operating Supply Voltage ($V_P - V_N$)	6.0	V
Operating Temperature Range	-40 to +85	°C
Storage Temperature Range	-65 to +150	°C
DC Voltage at any Channel Input	$(V_N - 0.5)$ to $(V_P + 0.5)$	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. STANDARD OPERATING CONDITIONS

Parameter	Rating	Units
Operating Temperature Range	-40 to +85	°C
Package Power Rating SOT143-4 Package (CM1293A-02SR) SC-74 Package (CM1293A-02SO, CM1293A-04SO) MSOP-10 Package (CM1293A-04MR)	225 225 400	mW

Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_P	Operating Supply Voltage ($V_P - V_N$)			3.3	5.5	V
I_P	Operating Supply Current	$(V_P - V_N) = 3.3$ V			8.0	μA
V_F	Diode Forward Voltage Top Diode Bottom Diode	$I_F = 8$ mA, $T_A = 25^\circ\text{C}$	0.60 0.60	0.80 0.80	0.95 0.95	V
I_{LEAK}	Channel Leakage Current	$T_A = 25^\circ\text{C}$, $V_P = 5$ V, $V_N = 0$ V		±0.1	±1.0	μA
C_{IN}	Channel Input Capacitance	At 1 MHz, $V_P = 3.3$ V, $V_N = 0$ V, $V_{IN} = 1.65$ V			2.0	pF
ΔC_{IO}	Channel I/O to I/O Capacitance			1.5		pF
V_{ESD}	ESD Protection – Peak Discharge Voltage at any Channel Input, in System Contact Discharge per IEC 61000-4-2 Standard Human Body Model, MIL-STD-883, Method 3015	$T_A = 25^\circ\text{C}$ (Notes 2 and 4) $T_A = 25^\circ\text{C}$ (Notes 3 and 4)	±8 ±15			kV
V_{CL}	Channel Clamp Voltage Positive Transients Negative Transients	$T_A = 25^\circ\text{C}$, $I_{PP} = 1$ A, $t_P = 8/20$ μS (Note 4)		+9.9 -1.6		V
R_{DYN}	Dynamic Resistance Positive Transients Negative Transients	$T_A = 25^\circ\text{C}$, $I_{PP} = 1$ A, $t_P = 8/20$ μS (Note 4)		0.96 0.5		Ω

1. All parameters specified at $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$ unless otherwise noted.
2. Standard IEC 61000-4-2 with $C_{Discharge} = 150$ pF, $R_{Discharge} = 330$ Ω, $V_P = 3.3$ V, V_N grounded.
3. Human Body Model per MIL-STD-883, Method 3015, $C_{Discharge} = 100$ pF, $R_{Discharge} = 1.5$ kΩ, $V_P = 3.3$ V, V_N grounded.
4. These measurements performed with no external capacitor on V_P .

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Table 5. ELECTRICAL OPERATING CHARACTERISTICS FOR CM1293A-02SO (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_P	Operating Supply Voltage ($V_P - V_N$)			3.3	5.5	V
I_P	Operating Supply Current	$(V_P - V_N) = 3.3\text{ V}$			8.0	μA
V_F	Diode Forward Voltage	$I_F = 8\text{ mA}$, $T_A = 25^\circ\text{C}$		0.90		V
I_{LEAK}	Channel Leakage Current	$T_A = 25^\circ\text{C}$, $V_P = 5\text{ V}$, $V_N = 0\text{ V}$		± 0.1	± 1.0	μA
C_{IN}	Channel Input Capacitance	At 1 MHz, $V_P = 3.3\text{ V}$, $V_N = 0\text{ V}$, $V_{IN} = 1.65\text{ V}$			2.0	pF
ΔC_{IO}	Channel I/O to I/O Capacitance			1.5		pF
V_{ESD}	ESD Protection Peak Discharge Voltage at any Channel Input, in System Contact Discharge per IEC 61000-4-2 Standard	$T_A = 25^\circ\text{C}$ (Notes 2 and 3)	± 8			kV
V_{CL}	Channel Clamp Voltage Positive Transients Negative Transients	$T_A = 25^\circ\text{C}$, $I_{PP} = 1\text{ A}$, $t_P = 8/20\text{ }\mu\text{S}$ (Note 3)		+9.9 -1.6		V
R_{DYN}	Dynamic Resistance Positive Transients Negative Transients	$T_A = 25^\circ\text{C}$, $I_{PP} = 1\text{ A}$, $t_P = 8/20\text{ }\mu\text{S}$ (Note 3)		0.96 0.5		Ω

1. All parameters specified at $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$ unless otherwise noted.
2. Standard IEC 61000-4-2 with $C_{Discharge} = 150\text{ pF}$, $R_{Discharge} = 330\text{ }\Omega$, $V_P = 3.3\text{ V}$, V_N grounded.
3. These measurements performed with no external capacitor on V_P .

PERFORMANCE INFORMATION

Input Channel Capacitance Performance Curves

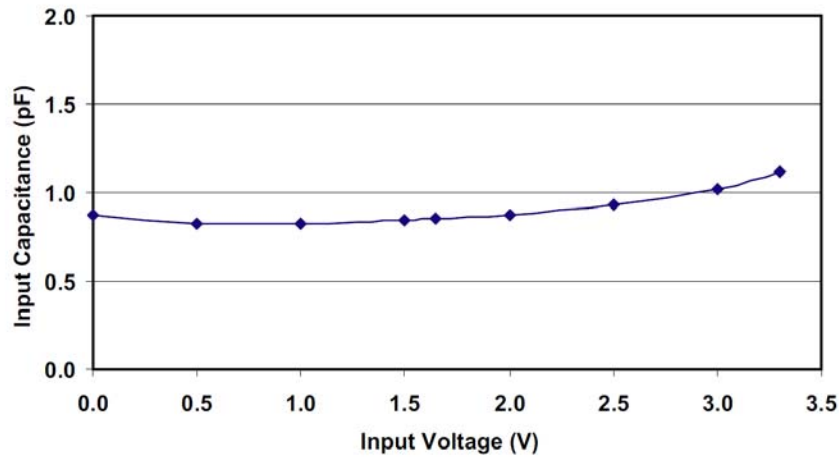


Figure 1. Typical Variation of C_{IN} vs. V_{IN}
 ($f = 1 \text{ MHz}$, $V_P = 3.3 \text{ V}$, $V_N = 0 \text{ V}$, $0.1 \mu\text{F}$ Chip Capacitor between V_P and V_N , 25°C)

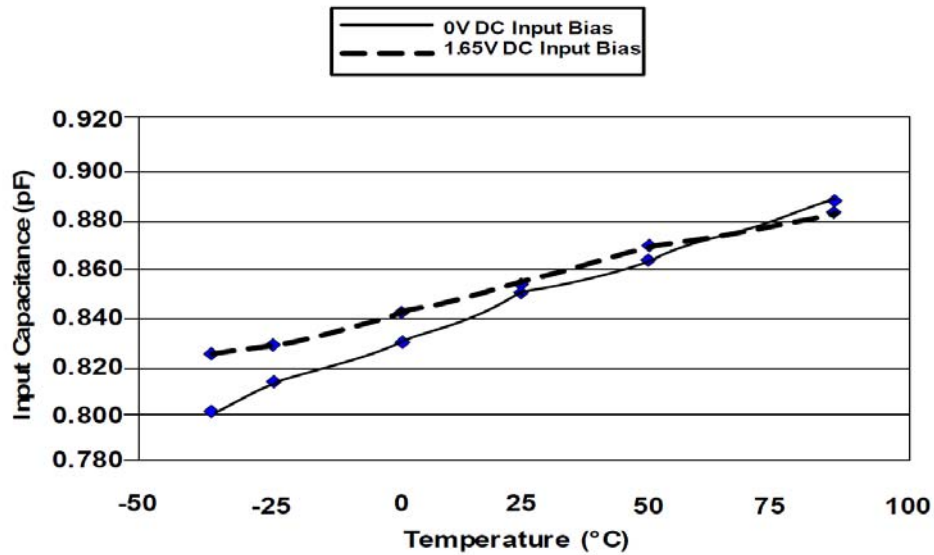


Figure 2. Typical Variation of C_{IN} vs. Temp
 ($f = 1 \text{ MHz}$, $V_{IN} = 30 \text{ mV}$, $V_P = 3.3 \text{ V}$, $V_N = 0 \text{ V}$, $0.1 \mu\text{F}$ Chip Capacitor between V_P and V_N)

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PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance (nominal conditions unless specified otherwise, 50 Ω Environment)

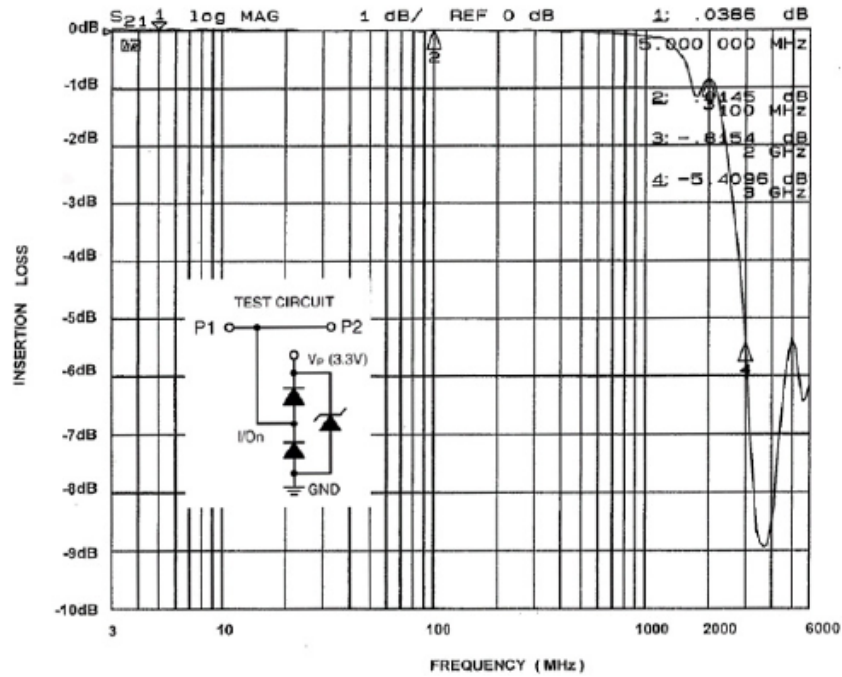


Figure 3. Insertion Loss (S21) vs. Frequency (0 V DC Bias, $V_p = 3.3$ V)

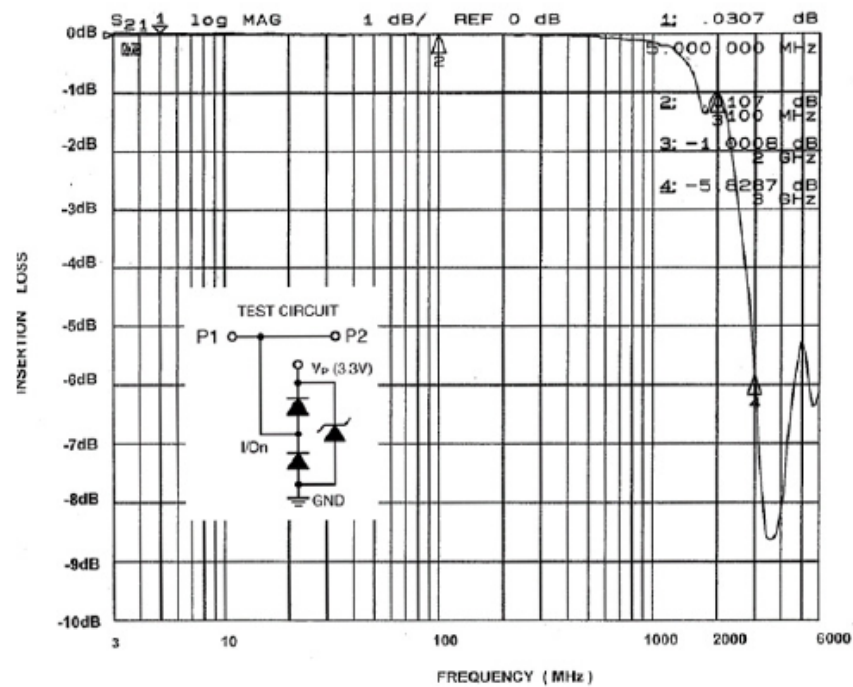


Figure 4. Insertion Loss (S21) vs. Frequency (2.5 V DC Bias, $V_p = 3.3$ V)

APPLICATION INFORMATION

Design Considerations

In order to realize the maximum protection against ESD pulses, care must be taken in the PCB layout to minimize parasitic series inductances on the Supply/Ground rails as well as the signal trace segment between the signal input (typically a connector) and the ESD protection device. Refer to Figure 5, which illustrates an example of a positive ESD pulse striking an input channel. The parasitic series inductance back to the power supply is represented by L_1 and L_2 . The voltage V_{CL} on the line being protected is:

$$V_{CL} = \text{Fwd voltage drop of } D_1 + V_{\text{SUPPLY}} + L_1 \times d(I_{\text{ESD}}) / dt + L_2 \times d(I_{\text{ESD}}) / dt$$

where I_{ESD} is the ESD current pulse, and V_{SUPPLY} is the positive supply voltage.

An ESD current pulse can rise from zero to its peak value in a very short time. As an example, a level 4 contact discharge per the IEC61000-4-2 standard results in a current pulse that rises from zero to 30 Amps in 1 ns. Here $d(I_{\text{ESD}})/dt$ can be approximated by $\Delta I_{\text{ESD}}/\Delta t$, or $30/(1 \times 10^{-9})$. So just 10 nH of series inductance (L_1 and L_2 combined) will lead to a 300 V increment in V_{CL} !

Similarly for negative ESD pulses, parasitic series inductance from the V_N pin to the ground rail will lead to drastically increased negative voltage on the line being protected.

The CM1293 has an integrated Zener diode between V_P and V_N . This greatly reduces the effect of supply rail inductance L_2 on V_{CL} by clamping V_P at the breakdown voltage of the Zener diode. However, for the lowest possible V_{CL} , especially when V_P is biased at a voltage significantly below the Zener breakdown voltage, it is recommended that a 0.22 μF ceramic chip capacitor be connected between V_P and the ground plane.

As a general rule, the ESD Protection Array should be located as close as possible to the point of entry of expected electrostatic discharges. The power supply bypass capacitor mentioned above should be as close to the V_P pin of the Protection Array as possible, with minimum PCB trace lengths to the power supply, ground planes and between the signal input and the ESD device to minimize stray series inductance.

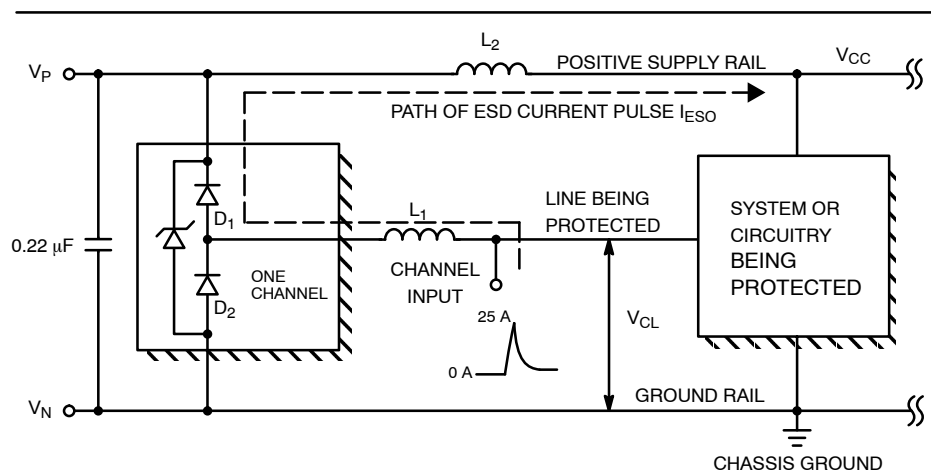
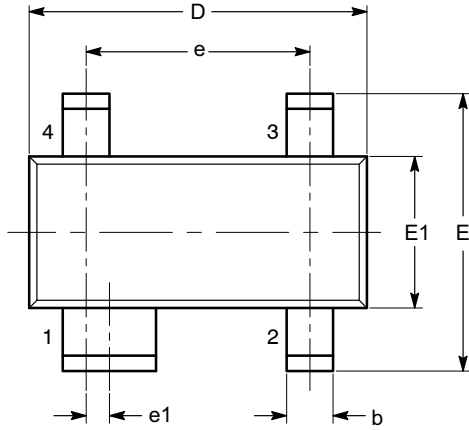


Figure 5. Application of Positive ESD Pulse between Input Channel and Ground

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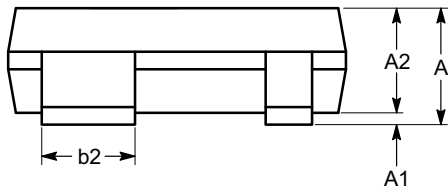
PACKAGE DIMENSIONS

SOT-143, 4 Lead
CASE 527AF-01
ISSUE A

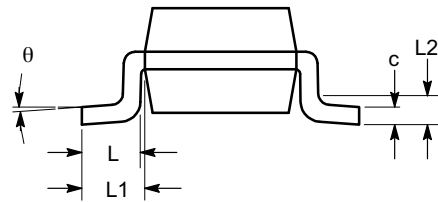


TOP VIEW

SYMBOL	MIN	NOM	MAX
A	0.80		1.22
A1	0.05		0.15
A2	0.75	0.90	1.07
b	0.30		0.50
b2	0.76		0.89
c	0.08		0.20
D	2.80	2.90	3.04
E	2.10		2.64
E1	1.20	1.30	1.40
e	1.92 BSC		
e1	0.20 BSC		
L	0.40	0.50	0.60
L1	0.54 REF		
L2		0.25	
θ	0°		8°



SIDE VIEW



END VIEW

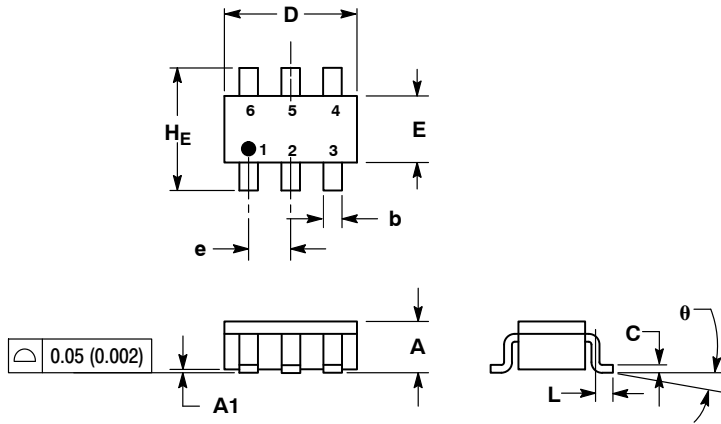
Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC TO-253.

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PACKAGE DIMENSIONS

SC-74
CASE 318F-05
ISSUE M

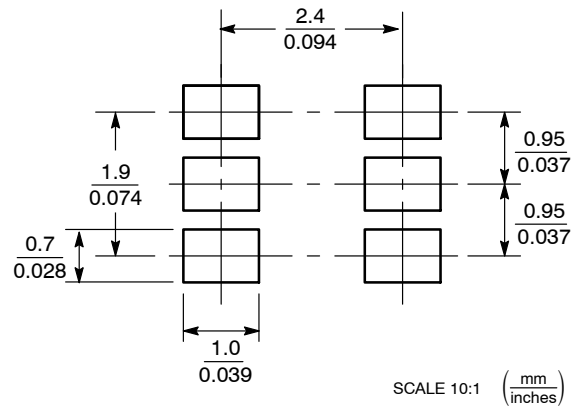


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
H_E	2.50	2.75	3.00	0.099	0.108	0.118
theta	0°	—	10°	0°	—	10°

SOLDERING FOOTPRINT*

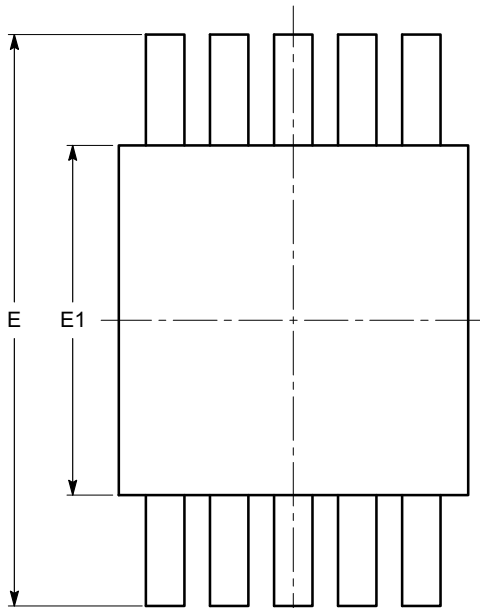


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

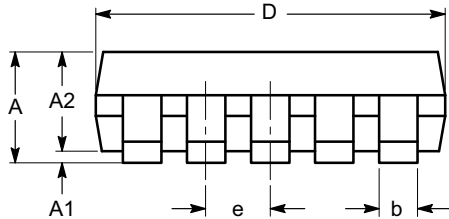
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PACKAGE DIMENSIONS

MSOP 10, 3x3
CASE 846AE-01
ISSUE O

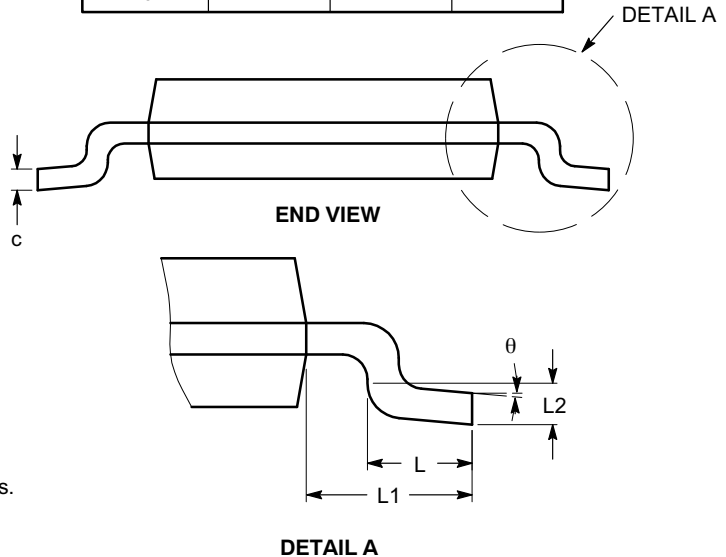


TOP VIEW



SIDE VIEW

SYMBOL	MIN	NOM	MAX
A			1.10
A1	0.00	0.05	0.15
A2	0.75	0.85	0.95
b	0.17		0.27
c	0.13		0.23
D	2.90	3.00	3.10
E	4.75	4.90	5.05
E1	2.90	3.00	3.10
e	0.50 BSC		
L	0.40	0.60	0.80
L1	0.95 REF		
L2	0.25 BSC		
θ	0°		8°



Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-187.

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